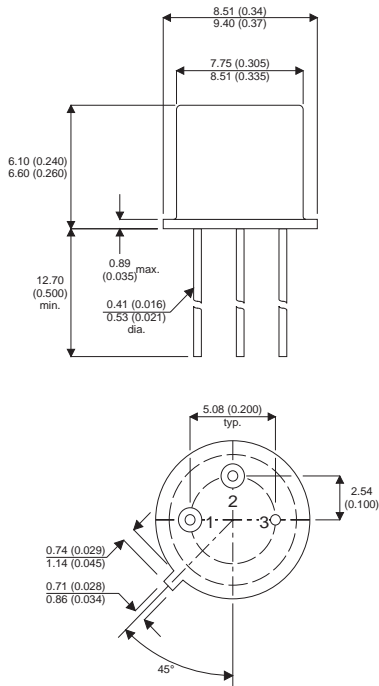


MECHANICAL DATA

Dimensions in mm (inches)



TO-39 (TO205AD)

Underside View

PIN 1 – Emitter PIN 2 – Base PIN 3 – Collector

PNP SILICON TRANSISTOR

FEATURES

- **High Voltage**
- **Hermetic TO39 Package**
- **Full Screening Options Available**

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

V_{CBO}	Collector – Base Voltage ($I_E = 0$)	-300V
V_{CEO}	Collector – Emitter Voltage ($I_B = 0$)	-300V
V_{EBO}	Emitter – Base Voltage ($I_B = 0$)	-5V
I_C	Collector Current	-0.5A
P_D	Total Device Dissipation $T_C = 50^{\circ}C$	5W
T_{stg}	Storage Temperature	-65 to 150°C
T_J	Junction Temperature	200°C
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	200°C/W
$R_{\theta JC}$	Thermal Resistance Junction to Case	30°C/W

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

Parameter		Test Conditions	Min	Typ	Max	Unit
$V_{(BR)CEO}$	Collector – Emitter Breakdown Voltage	$I_C = -10mA, I_B = 0$	-300			V
I_{CBO}	Collector Cut-off Current	$V_{CB} = -200V, I_E = 0$			-5	μA
I_{EBO}	Emitter Cut-off Current	$V_{BE} = -3V, I_C = 0$			-5	μA
$V_{CE(sat)*}$	Collector – Emitter Saturation Voltage	$I_C = -10mA, I_B = -1.0mA$			-0.5	V
		$I_C = -100mA, I_B = -10mA$			-1.4	
		$I_C = -500mA, I_B = -100mA$			-5.0	
$V_{BE(sat)*}$	Base – Emitter Saturation Voltage	$I_C = -10mA, I_B = -1.0mA$			-0.8	V
		$I_C = -100mA, I_B = -10mA$			-0.9	
		$I_C = -500mA, I_B = -100mA$			-1.2	
h_{FE*}	DC Current Gain	$V_{CE} = -10V, I_C = -1.0mA$	30			—
		$V_{CE} = -10V, I_C = -10mA$	50		150	
		$V_{CE} = -10V, I_C = -100mA$	50			

DYNAMIC CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

Parameter		Test Conditions	Min.	Typ.	Max.	Unit
f_T	Transition Frequency	$I_C = -15mA, V_{CE} = -10V, f = 35MHz$		70		MHz
C_c	Collector Capacitance	$V_{CB} = -20V, I_E = 0, f = 1MHz$			15	pF
t_{on}	Turn on Time	$V_{CC} = -31V, I_C = -50mA, I_{B1} = I_{B2} = 5mA$		125		ns
		$V_{CC} = -31V, I_C = -500mA, I_{B1} = I_{B2} = 100mA$		125		ns
t_{off}	Turn off Time	$V_{CC} = -31V, I_C = -50mA, I_{B1} = I_{B2} = 5mA$		850		ns
		$V_{CC} = -31V, I_C = -500mA, I_{B1} = I_{B2} = 100mA$		125		ns

(*) Pulse test : Pulse Width < 300 μs ,Duty Cycle < 2%